

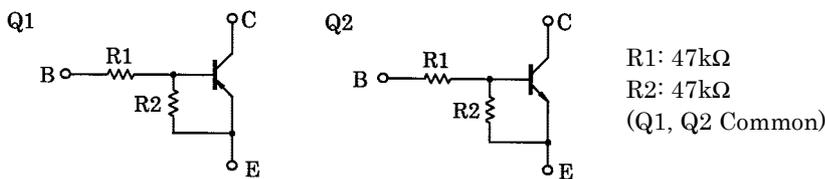
TOSHIBA Transistor
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

RN4604

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Including two devices in SM6 (super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values



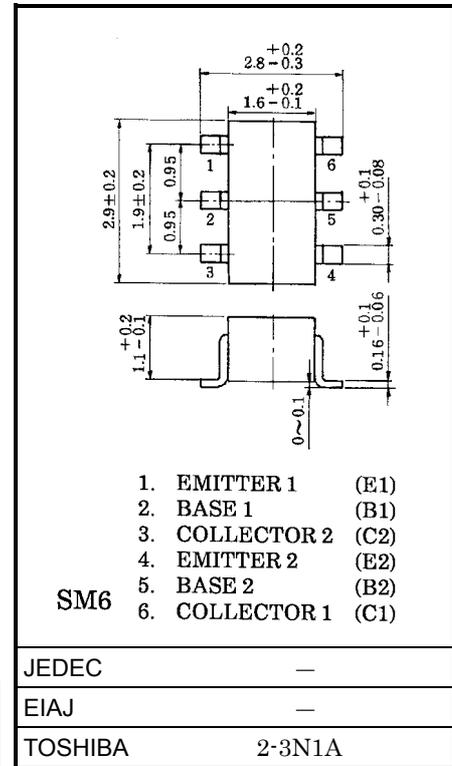
Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-10	V
Collector current	I_C	-100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	100	mA

Unit in mm



Weight: 0.015g

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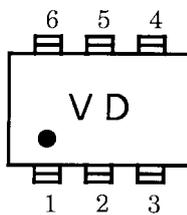
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Q1, Q2 Common Maximum Ratings (Ta = 25°C)

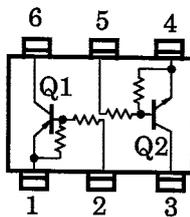
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P_C *	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

* Total rating

Marking



Equivalent Circuit (Top View)



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- The information contained herein is subject to change without notice.

Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CBO}	—	V _{CB} = -50V, I _E = 0	—	—	-100	nA
	I _{CEO}	—	V _{CE} = -50V, I _B = 0	—	—	-500	
Emitter cut-off current	I _{EBO}	—	V _{EB} = -10V, I _C = 0	-0.082	—	-0.15	mA
DC current gain	h _{FE}	—	V _{CE} = -5V, I _C = -10mA	80	—	—	—
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V
Input voltage (ON)	V _{I (ON)}	—	V _{CE} = -0.2V, I _C = -5mA	-1.5	—	-5.0	V
Input voltage (OFF)	V _{I (OFF)}	—	V _{CE} = -5V, I _C = -0.1mA	-1.0	—	-1.5	V
Transition frequency	f _T	—	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF

Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CBO}	—	V _{CB} = 50V, I _E = 0	—	—	100	nA
	I _{CEO}	—	V _{CE} = 50V, I _B = 0	—	—	500	
Emitter cut-off current	I _{EBO}	—	V _{EB} = 10V, I _C = 0	0.082	—	0.15	mA
DC current gain	h _{FE}	—	V _{CE} = 5V, I _C = 10mA	80	—	—	—
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = 5mA, I _B = 0.25mA	—	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	—	V _{CE} = 0.2V, I _C = 5mA	1.5	—	5.0	V
Input voltage (OFF)	V _{I (OFF)}	—	V _{CE} = 5V, I _C = 0.1mA	1.0	—	1.5	V
Transition frequency	f _T	—	V _{CE} = 10V, I _C = 5mA	—	250	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = 10V, I _E = 0, f = 1 MHz	—	3	6	pF

Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	—	32.9	47	61.1	kΩ
Resistor ratio	R1/R2	—	—	0.9	1.0	1.1	—

